



## Description

The HXY4012GD uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = 40V$   $I_D = 20A$

$R_{DS(ON)} < 24m\Omega$  @  $V_{GS}=10V$

$V_{DS} = -40V$   $I_D = -20A$

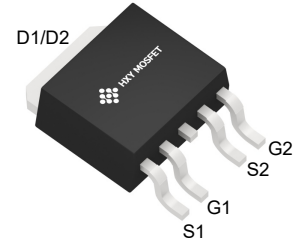
$R_{DS(ON)} < 38m\Omega$  @  $V_{GS}=-10V$

## Application

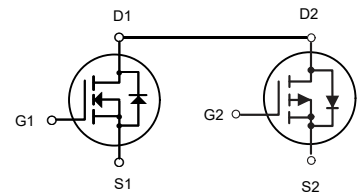
Wireless charging

Boost driver

Brushless motor



TO-252-4L



N-Channel MOSFET

P-Channel MOSFET

## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HXY4012GD	TO-252-4L	HXY MOSFET	2500

## Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V <sub>DS</sub>	Drain-Source Voltage	40	-40	V
V <sub>GS</sub>	Gate-Source Voltage	±20	±20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	20	-20	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	16.5	-16.5	A
IDM	Pulsed Drain Current <sup>2</sup>	40	-40	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	40	40	W
TSTG	Storage Temperature Range	-55 to 150	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	-55 to 150	°C
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	62		°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	3.1		°C/W



**N-CH Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=10A$	-	18	24	m $\Omega$
		$V_{GS}=4.5V, I_D=5A$	-	26	37	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=10A$		15	-	S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	1500	-	PF
Output Capacitance	$C_{oss}$		-	215	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	135	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, R_L=2\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	4	-	nS
Turn-on Rise Time	$t_r$		-	11.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	18	-	nS
Turn-Off Fall Time	$t_f$		-	5.6	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=20V, I_D=10A,$ $V_{GS}=10V$	-	24	-	nC
Gate-Source Charge	$Q_{gs}$		-	4	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3.5	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=10A$	-	0.8	1.2	V



### P-CH Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-7A$	-	33	38	m $\Omega$
		$V_{GS}=-4.5V, I_D=-4A$	-	37	49	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-7A$	-	15	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-20V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	1225	-	PF
Output Capacitance	$C_{oss}$		-	190	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	120	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=2.3\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	10	-	nS
Turn-on Rise Time	$t_r$		-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	$t_f$		-	18	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-20V, I_D=-7A$ $V_{GS}=-10V$	-	21	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.5	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3.0	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-14A$	-	-	-1.2	V

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production



### N- Channel Typical Electrical and Thermal Characteristics (Curves)

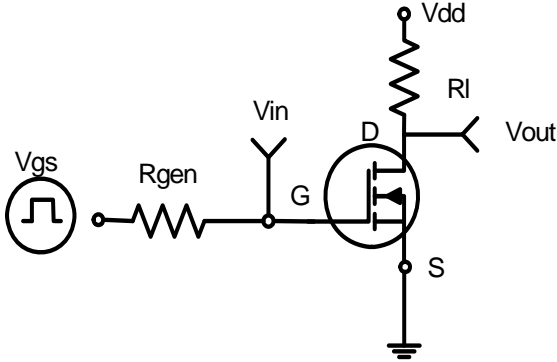


Figure 1: Switching Test Circuit

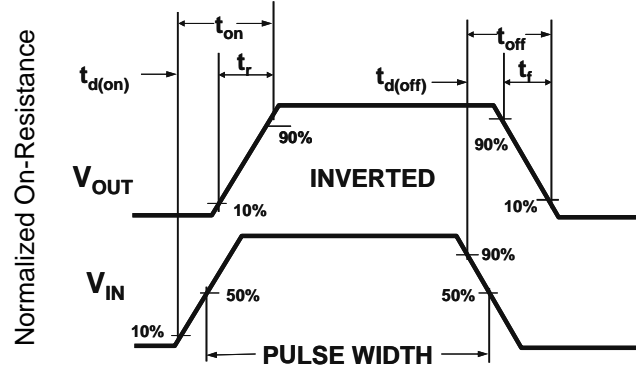


Figure 2: Switching Waveforms

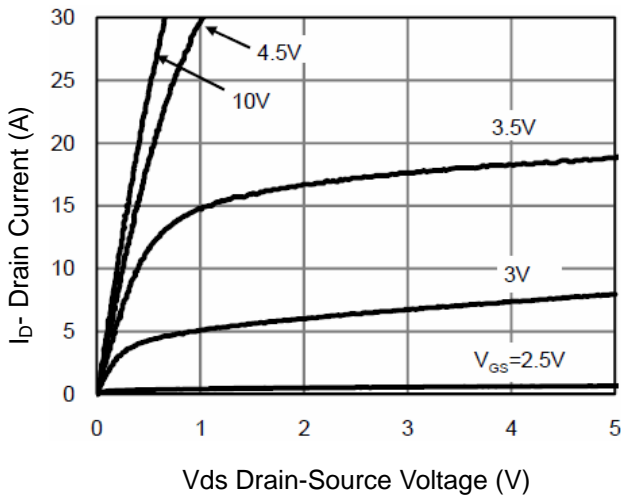


Figure 3 Output Characteristics

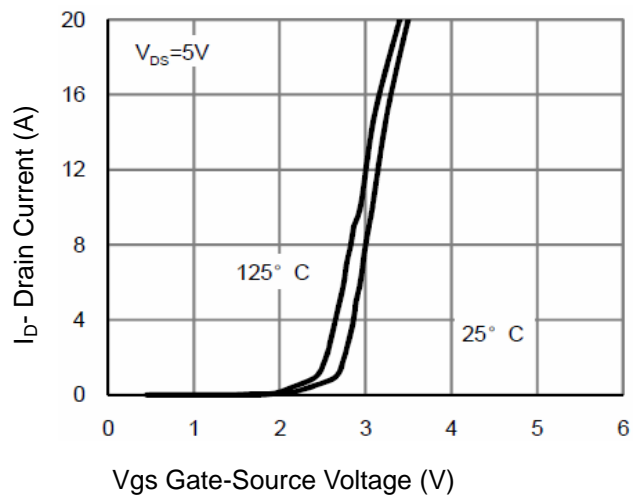


Figure 4 Transfer Characteristics

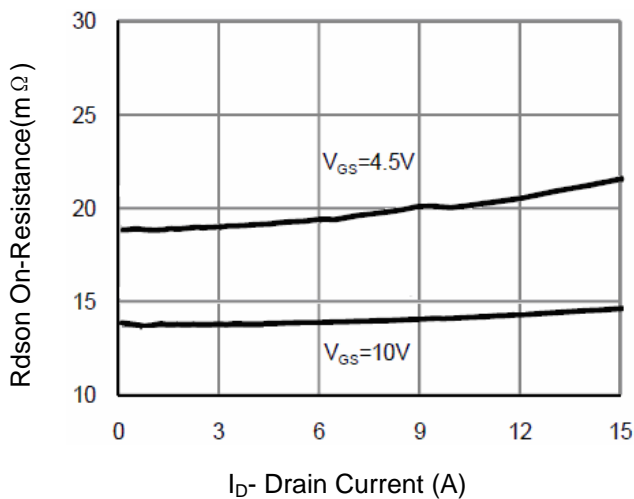


Figure 5 Drain-Source On-Resistance

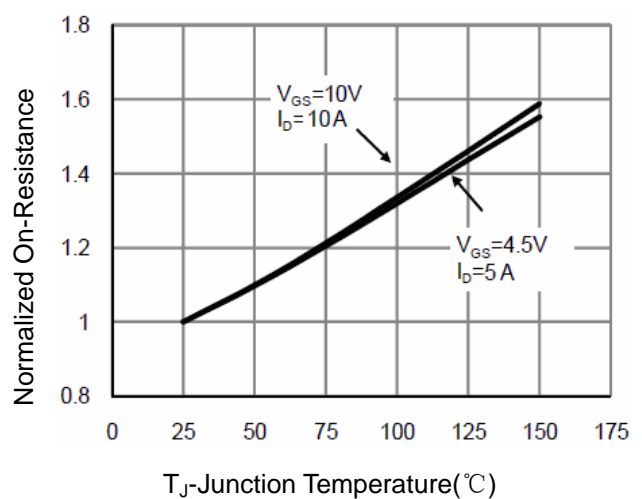
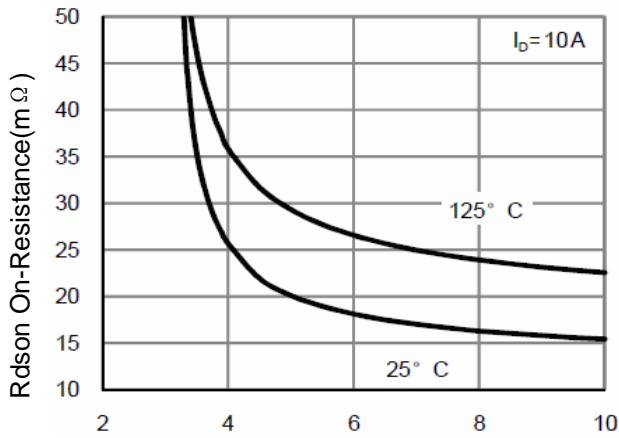
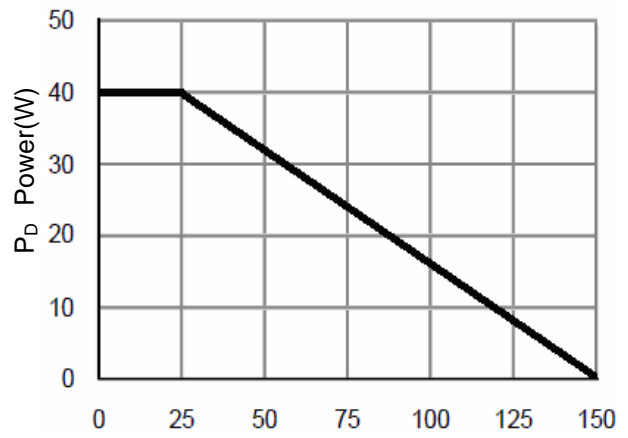


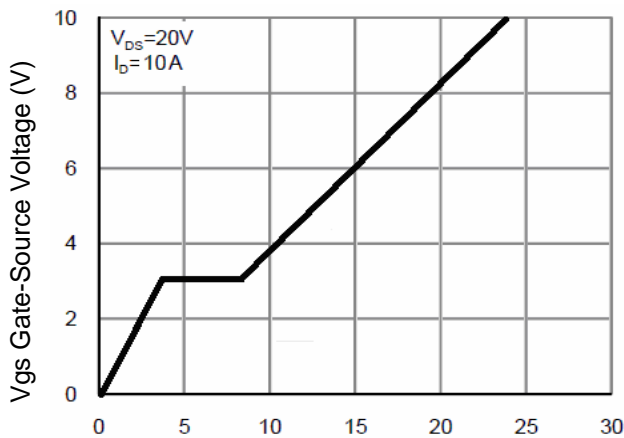
Figure 6 Drain-Source On-Resistance



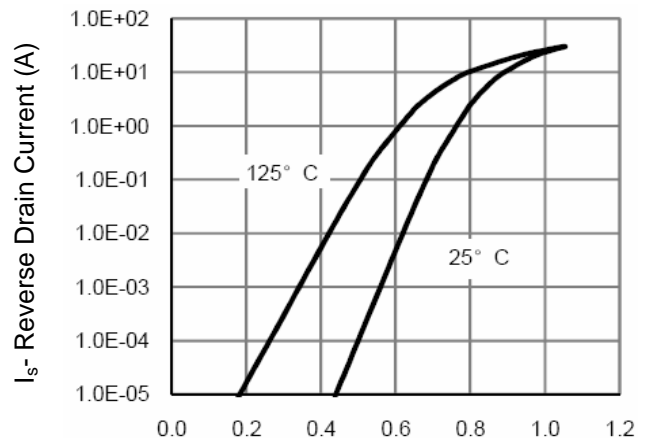
Vgs Gate-Source Voltage (V)  
**Figure 7 Rdson vs Vgs**



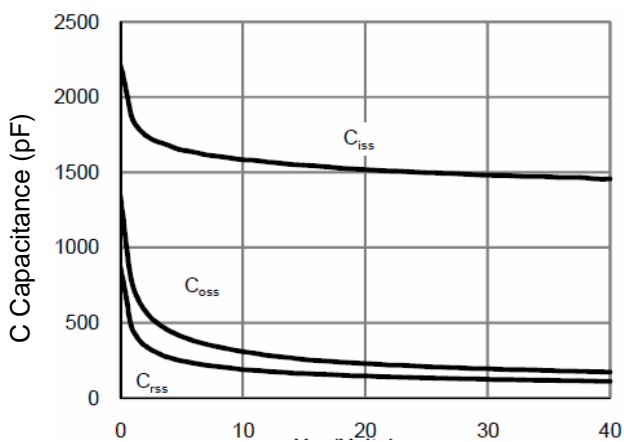
Tj Junction Temperature (°C)  
**Figure 8 Power Dissipation**



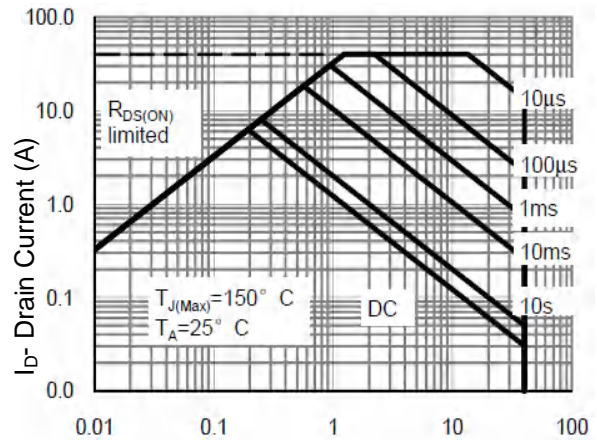
Qg Gate Charge (nC)  
**Figure 9 Gate Charge**



Vds Drain-Source Voltage (V)  
**Figure 10 Source-Drain Diode Forward**



Vds Drain-Source Voltage (V)  
**Figure 11 Capacitance vs Vds**



Vds Drain-Source Voltage (V)  
**Figure 12 Safe Operation Area**

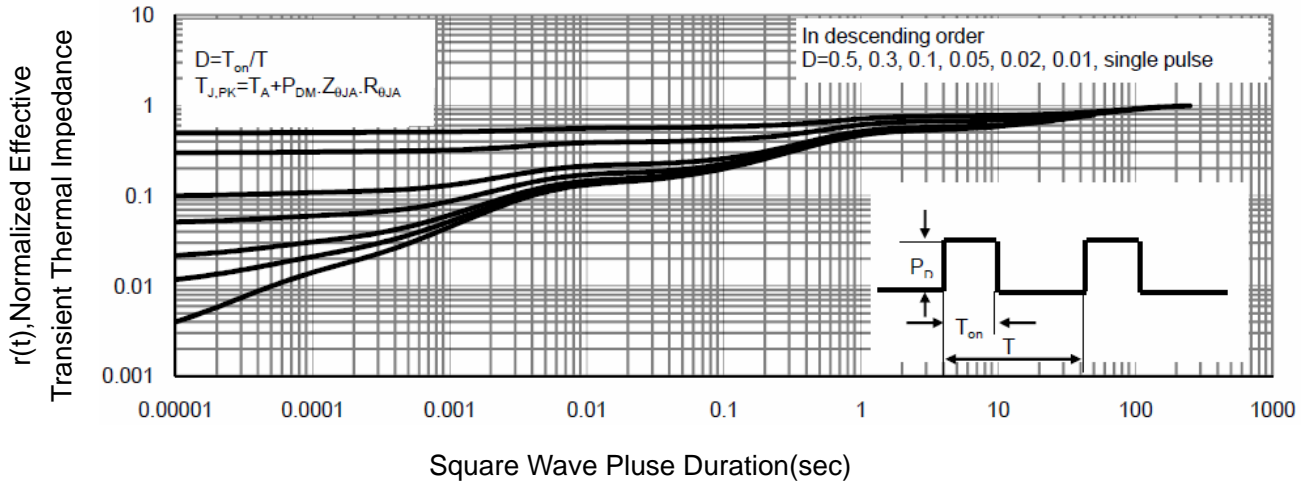


Figure 13 Normalized Maximum Transient Thermal Impedance



### P- Channel Typical Electrical and Thermal Characteristics (Curves)

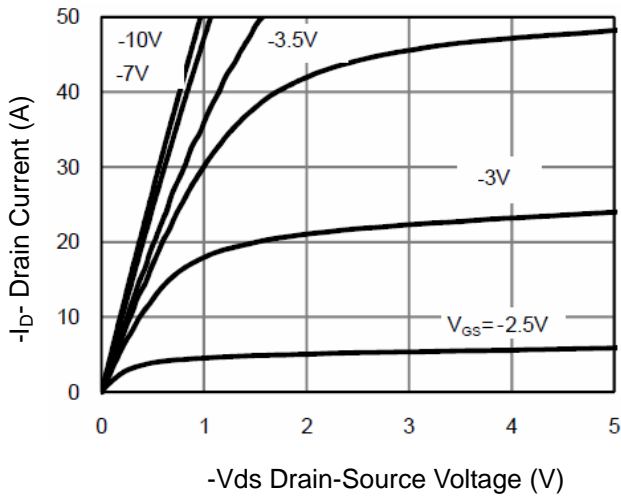


Figure 1 Output Characteristics

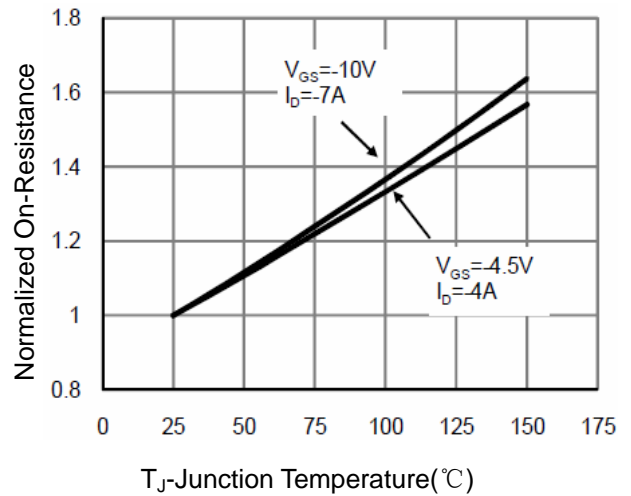


Figure 4 Rdson-Junction Temperature

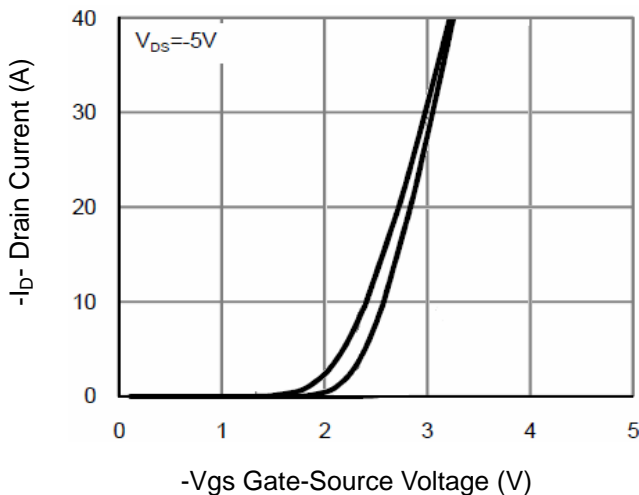


Figure 2 Transfer Characteristics

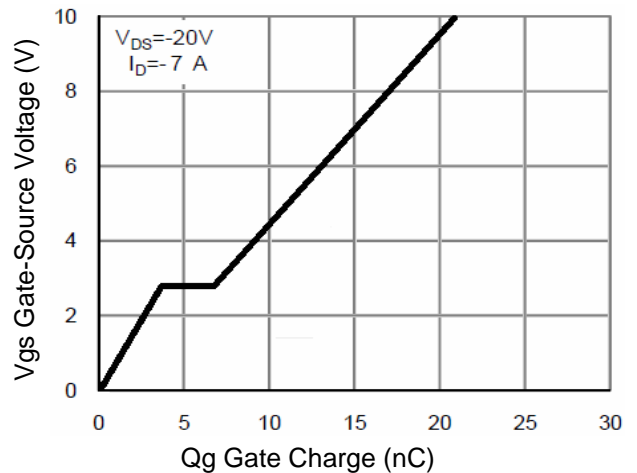


Figure 5 Gate Charge

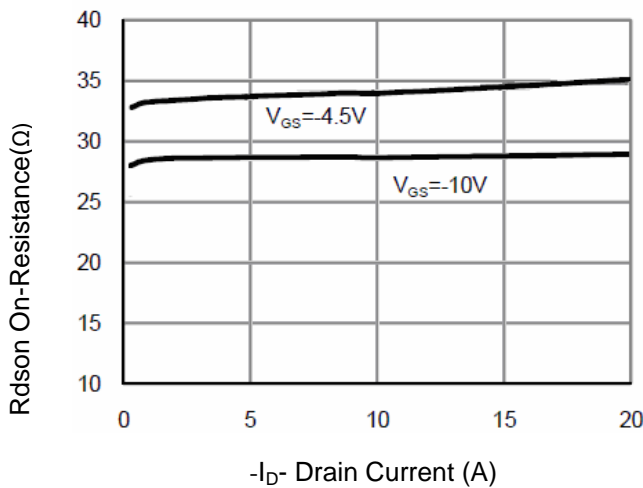


Figure 3 Rdson- Drain Current

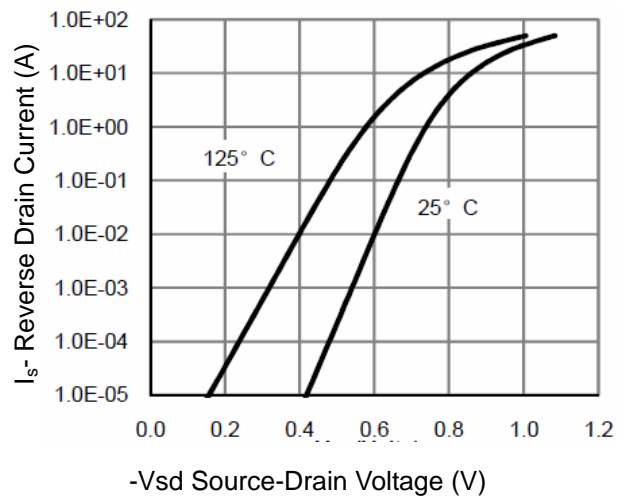


Figure 6 Source- Drain Diode Forward

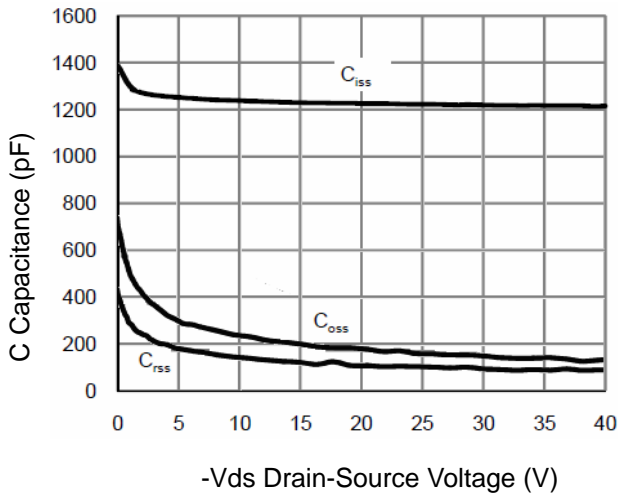


Figure 7 Capacitance vs Vds

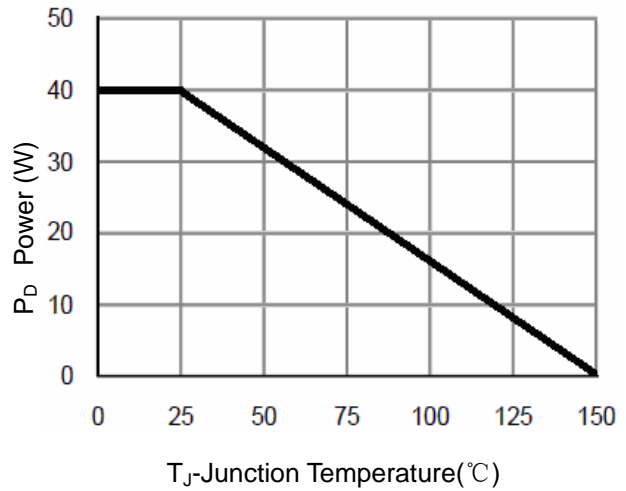


Figure 9 Power Dissipation

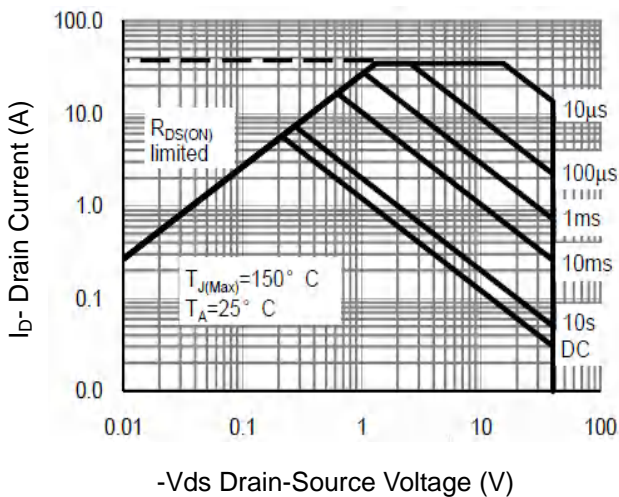


Figure 8 Safe Operation Area

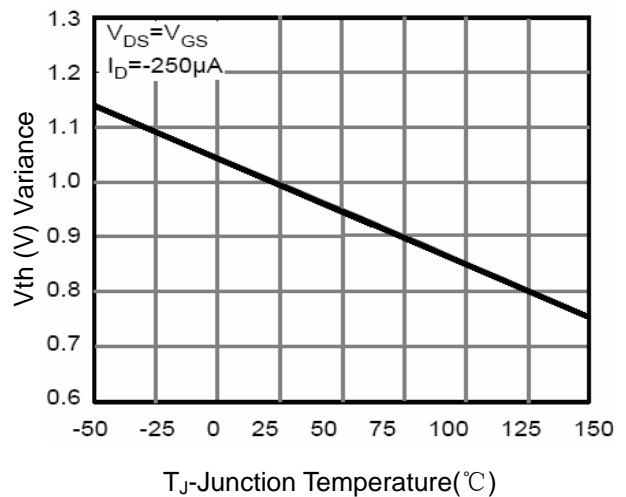


Figure 10  $V_{GS(th)}$  vs Junction Temperature

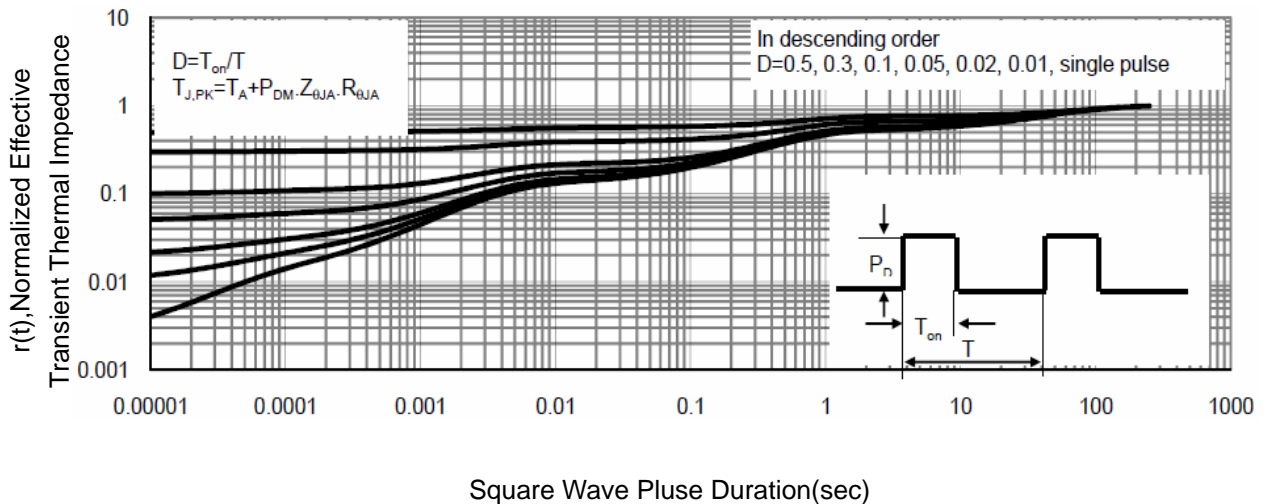
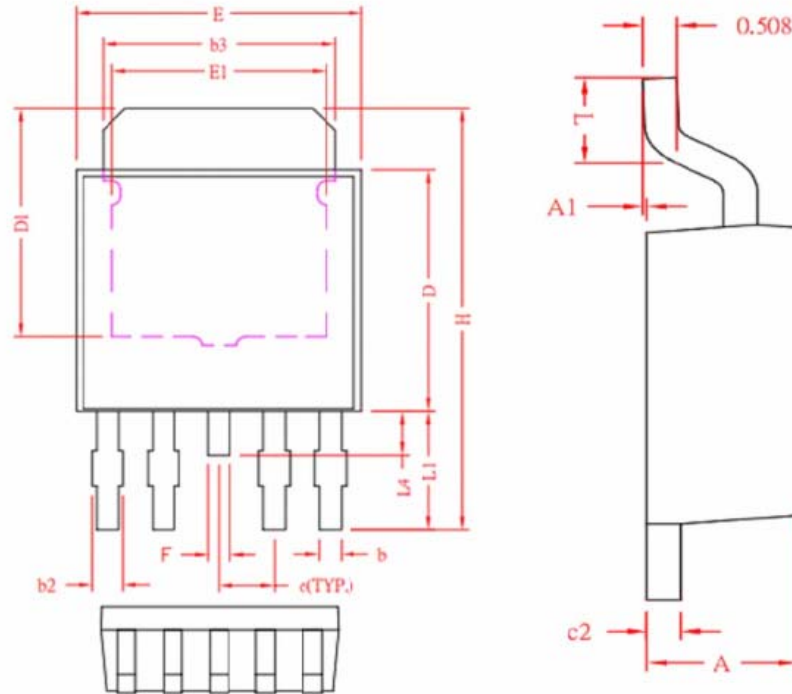


Figure 11 Normalized Maximum Transient Thermal Impedance



### TO-252-4L Package Information



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0	0.08	0.15
b	0.45	0.53	0.60
b2	0.50	0.65	0.80
b3	5.20	5.35	5.50
c2	0.45	0.50	0.55
D	5.40	5.60	5.80
D1	4.57	-	-
E	6.40	6.60	6.80
E1	3.81	-	-
e	1.27 REF.		
F	0.40	0.50	0.60
H	9.40	9.80	10.20
L	1.40	1.59	1.77
L1	2.40	2.70	3.00
L4	0.80	1.00	1.20



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